

TOSHIBA PHOTO DIODE SILICON PN

TPS721A

LIGHT RECEIVING DEVICE FOR PLASTIC FIBER / POLYMER CLAD FIBER

Unit in mm

- Small dark current : $I_D = 0.5\text{nA}$ (Typ.)
- High current transfer ratio : $S_f = 0.36\text{A/W}$ (Typ.)
- High speed application is possible : $f_c = 70\text{MHz}$ (Typ.)

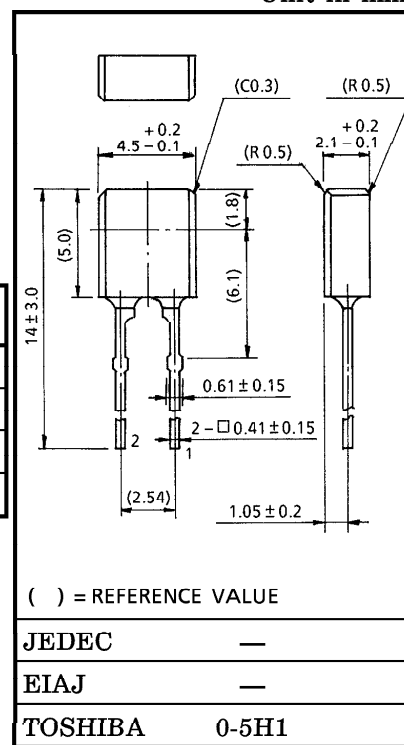
MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	50	V
Power Dissipation	P_D	150	mW
Operating Temperature Range	T_{opr}	$-30 \sim 85$	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-40 \sim 100$	$^\circ\text{C}$

PIN CONNECTION



1. CATHODE
2. ANODE



Weight : 0.12g (Typ.)

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Dark Current		I_D	$V_R = 10\text{V}$	—	0.5	8	nA
Fiber Coupling Sensitivity (Note)		S_f	$V_R = 10\text{V}$, $\lambda = 660\text{nm}$, $P_f = 1\mu\text{W}$	0.33	0.36	—	A/W
Peak Sensitivity Wavelength		λ_P	$V_R = 10\text{V}$	—	840	—	nm
Directional Angle Half Value Width		$\theta_{\frac{1}{2}}$	$V_R = 10\text{V}$	—	± 65	—	$^\circ$
Capacitance Between Terminals		C_T	$V_R = 10\text{V}$, $f = 1\text{MHz}$	—	10	—	pF
Switching Time	Rise Time	t_r	$V_R = 10\text{V}$, $R_L = 50\Omega$	—	4	—	ns
	Fall Time	t_f		—	4	—	
Cut-off Frequency		f_c	$V_R = 10\text{V}$, $R_L = 50\Omega$	—	70	—	MHz

Note : Plastic fiber used : Fiber length 0.5m, Core diameter 980 μm , NA 0.5.

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PRECAUTION

Please be careful of the followings.

1. Soldering temperature : 260°C MAX. Soldering time : 3s MAX.
(Soldering portion of lead : above 2.5mm from the body of the device)
2. If the lead is formed, the lead should be formed at a distance of 2.5mm from the body of the device.
Soldering shall be performed after lead forming.

